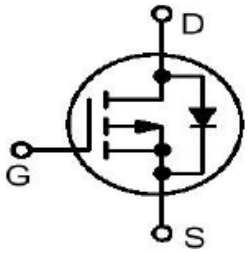
P-Channel Enhancement Mode MOSFET
TBL2301W

Features

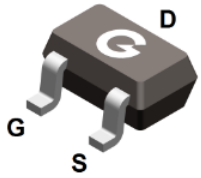
HF

- High-speed switching
- Drive circuits can be simple
- Parallel use is easy
- Halogen free
- Qualified to AEC-Q101 standards for high reliability



Typical Applications

- Power management in note book
- Switching application
- Battery powered system
- Load switch



SOT-323

Mechanical Data

- Case: SOT-323
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
TBL2301W	SOT-323	3000 pcs / Tape & Reel	2301

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	-20	V
Gate-to-Source Voltage	V_{GSS}	±12	V
Continuous Drain Current (T_A = 25°C) *1	I_D	-1.5	A
Continuous Drain Current (T_A = 70°C) *1		-1.2	A
Pulsed Drain Current (t_p = 10μs, T_A = 25°C)	I_{DM}	-10	A
Single Pulse Avalanche Energy *3	E_{AS}	3	mJ
Power Dissipation (T_A = 25°C) *1	P_D	0.25	W
Operating Junction Temperature Range	T_J	-55 ~ +150	°C
Storage Temperature Range	T_{STG}	-55 ~ +150	°C

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Air *1	$R_{\theta JA}$	-	-	500	°C/W

Electrical Characteristics (@ T_A = 25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = -250μA	-20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -20V, V_{GS} = 0V	-	-	-1	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS} = ±12V, V_{DS} = 0V	-	-	±100	nA
On Characteristics						
$R_{DS(ON)}$	Drain-Source On-resistance *2	V_{GS} = -4.5V, I_D = -2A	-	72	150	mΩ
		V_{GS} = -2.5V, I_D = -1.5A	-	90	200	
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = -250uA	-0.4	-0.7	-1.0	V
R_G	Gate Resistance	V_{GS} = 0V, f = 1MHz	-	27	-	Ω
Dynamic Characteristics						
C_{ISS}	Input Capacitance	V_{GS} = 0V V_{DS} = -15V f = 1.0MHz	-	538	-	pF
C_{OSS}	Output Capacitance		-	62	-	
C_{RSS}	Reverse Transfer Capacitance		-	55	-	
Switching Characteristics						
$t_{d(ON)}$	Turn-on Delay Time *4	V_{DD} = -10V V_{GS} = -4.5V I_D = -1A R_G = 10Ω	-	11	-	ns
t_r	Turn-on Rise Time *4		-	35	-	
$t_{d(OFF)}$	Turn-Off Delay Time *4		-	30	-	
t_f	Turn-Off Fall Time *4		-	10	-	
Q_G	Total Gate-Charge	V_{DD} = -10V V_{GS} = -4.5V I_D = -1.5A	-	6.5	-	nC
Q_{GS}	Gate to Source Charge		-	1.6	-	
Q_{GD}	Gate to Drain (Miller) Charge		-	1.4	-	
Source-Drain Diode Characteristics						
V_{SD}	Diode Forward Voltage *2	I_{SD} = -1.5A,V_{GS} = 0V	-	-0.8	-1.2	V

Notes:

1. The data tested by surface mounted on a minimum recommended FR-4 board
2. The data tested by pulsed, pulse width ≤ 300μs, duty cycle ≤ 2%
3. The E_{AS} data shows Max. rating. The test condition is V_{DD} = -10V, V_{GS} = -6V, L = 0.1mH
4. Guaranteed by design, not subject to production

Ratings and Characteristics Curves (@ T_A = 25°C unless otherwise specified)

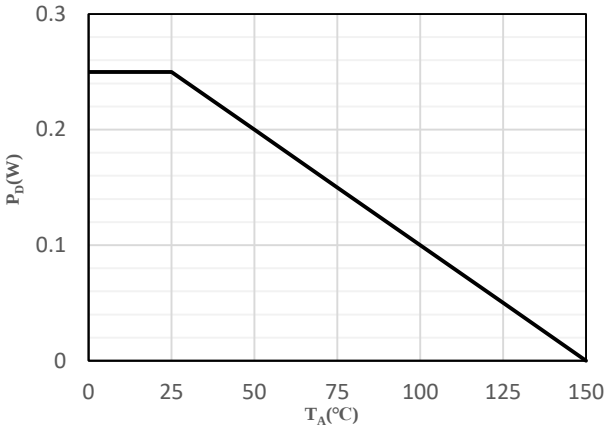


Fig 1 Power Dissipation

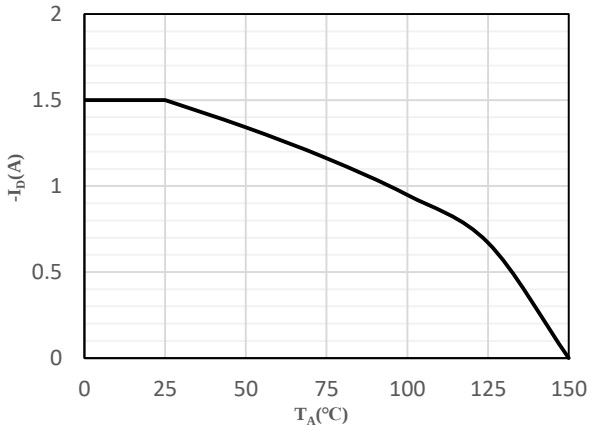


Fig 2 Drain Current

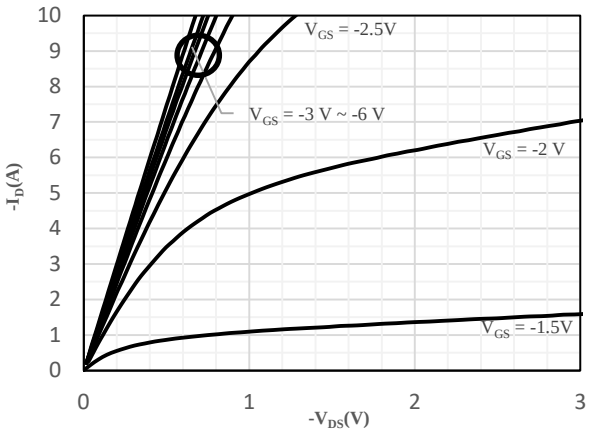


Fig 3 Typical Output Characteristics

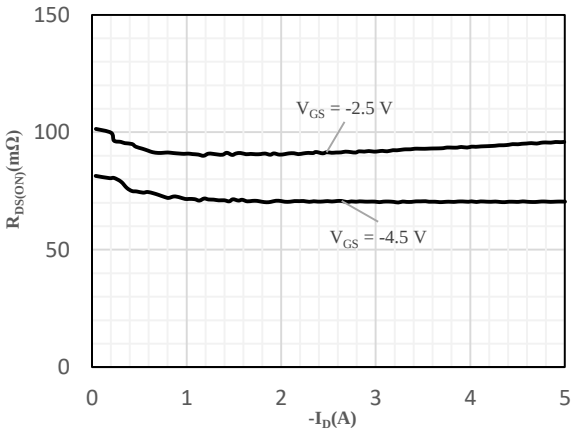


Fig 4 On-Resistance vs. Drain Current and Gate Voltage

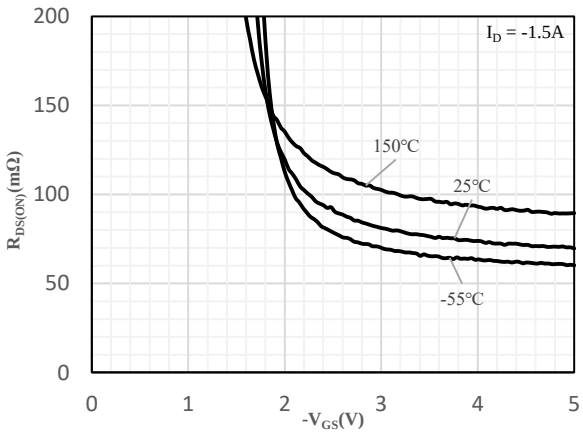


Fig 5 On-Resistance vs. Gate-Source Voltage

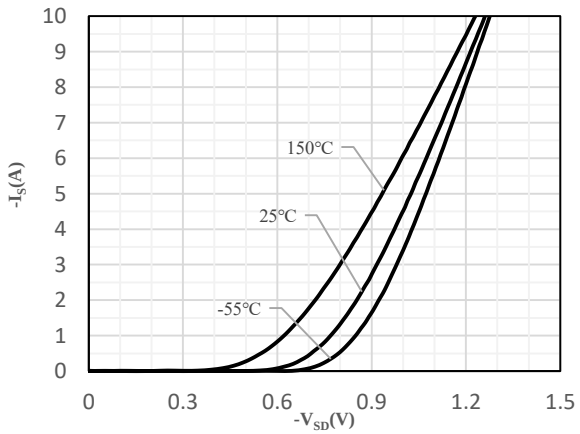


Fig 6 Body-Diode Characteristics

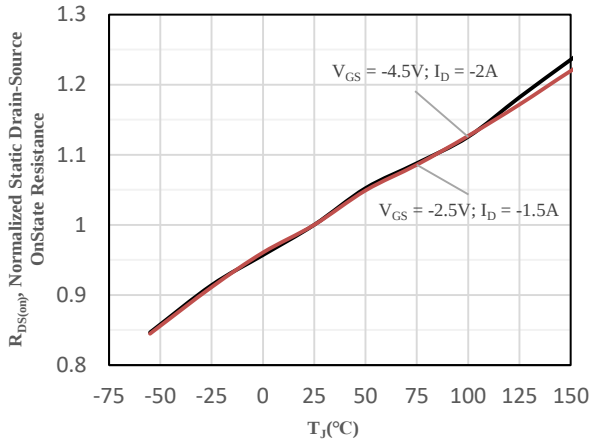


Fig 7 Normalized On-Resistance vs. Junction Temperature

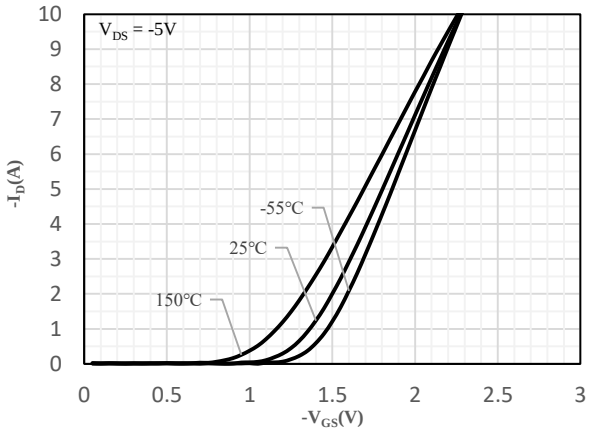


Fig 8 Transfer Characteristics

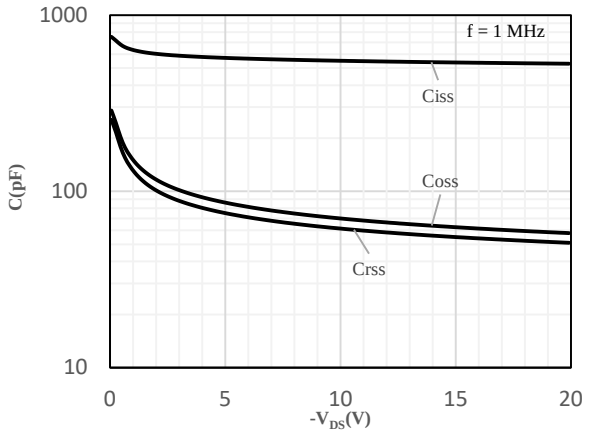


Fig 9 Capacitance Characteristics

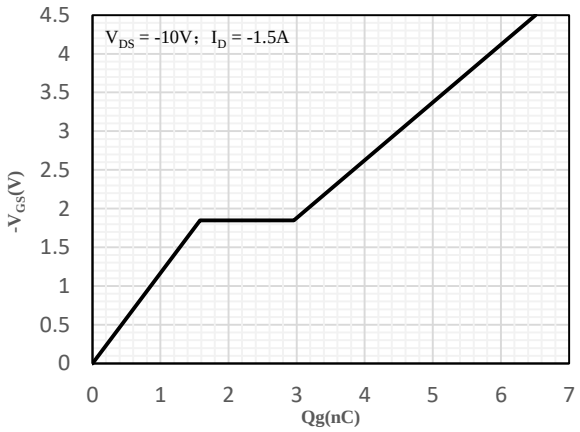


Fig 10 Gate-Charge Characteristics

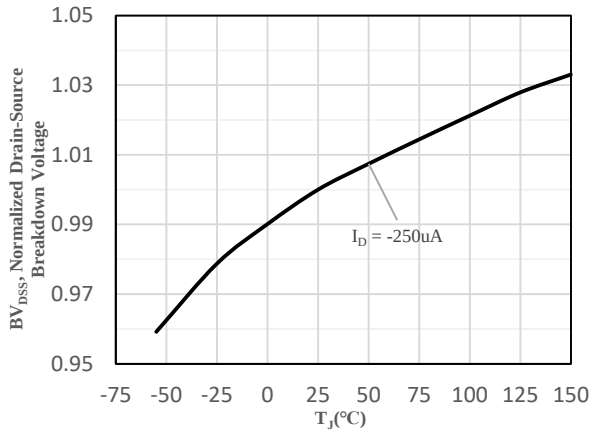


Fig 11 Normalized Breakdown Voltage vs. Junction Temperature

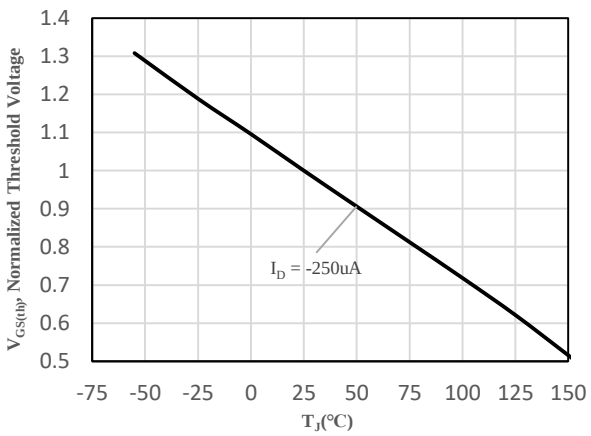
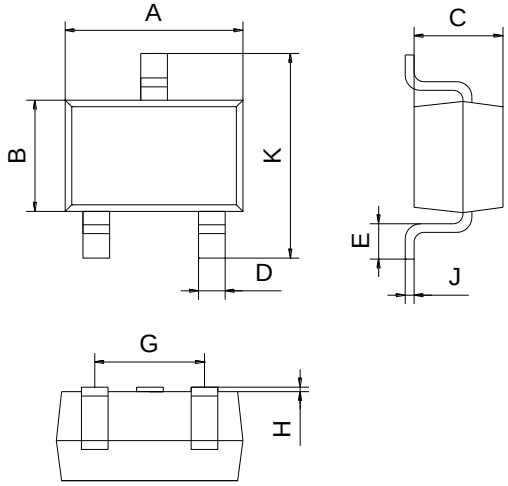


Fig 12 Normalized $V_{GS(th)}$ vs. Junction Temperature

Package Outline Dimensions (Unit: mm)



SOT-323		
Dimension	**Min.**	**Max.**
A	2.00	2.20
B	1.15	1.35
C	0.90	1.10
D	0.15	0.35
E	0.25	0.40
G	1.20	1.40
H	0.02	0.10
J	0.05	0.15
K	2.20	2.40

Mounting Pad Layout (Unit: mm)

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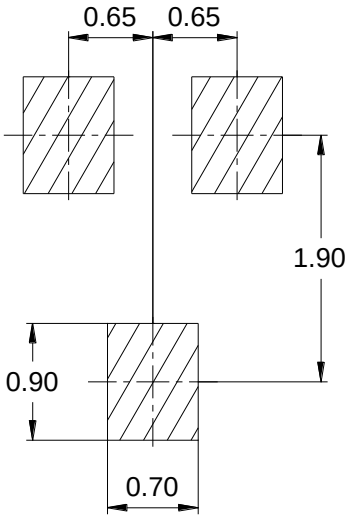

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